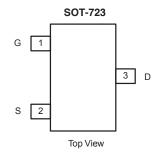
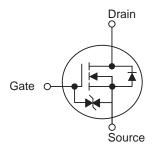


# N-Channel 60-V (D-S) MOSFET

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PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (mA)	
60	2 at V <sub>GS</sub> = 10 V	300	





#### **FEATURES**

Low On-Resistance: 2 Ω
Low Threshold: 2 V (typ.)
Low Input Canaditance: 25 pt

Low Input Capacitance: 25 pF

Fact Switching Capacit 25 pa

• Fast Switching Speed: 25 ns

- Low Input and Output LeakageDT-Trench Power MOSFET
- · Gate-Source ESD Protected
- Compliant to RoHS Directive 2002/95/EC

### **BENEFITS**

- · Low Offset Voltage
- · Low-Voltage Operation
- Easily Driven Without Buffer
- · High-Speed Circuits
- · Low Error Voltage

### **APPLICATIONS**

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- · Battery Operated Systems
- Solid-State Relays

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>b</sup>	T <sub>A</sub> = 25 °C	I_	300		
Continuous Diam Current (1, = 150°C)	T <sub>A</sub> = 100 °C	I <sub>D</sub>	190	mA	
Pulsed Drain Current <sup>a</sup>	•	I <sub>DM</sub>	800		
$T_A = 25$		P <sub>D</sub>	0.35	W	
Power Dissipation <sup>b</sup>	T <sub>A</sub> = 100 °C	' D	0.14	VV	
Maximum Junction-to-Ambient <sup>b</sup>		R <sub>thJA</sub>	350	°C/W	
Operating Junction and Storage Temperature Range		T <sub>J,</sub> T <sub>stg</sub>	- 55 to 150	°C	

#### Notes

- a. Pulse width limited by maximum junction temperature.
- b. Surface Mounted on FR4 board.

Pb-free

RoHS\*

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



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		erwise noted		Limits		
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static				•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1		2.5	V
	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 10	μА
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 15 \text{ V}$			1	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 150	nA
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			± 1000	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100	
Zana Oata Valtana Dasia Ourrent		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 60 V, $V_{GS}$ = 0 V , $T_{J}$ = 125 °C			500	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 7.5 V	800			mA
		V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V	500			
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 500 mA			2	Ω
Drain-Source On-Resistance <sup>a</sup>		$V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$			4	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA	100			mS
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 200 mA, V <sub>GS</sub> = 0 V			1.3	V
Dynamic <sup>a</sup>	_					
Total Gate Charge	Qg	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V $I_{D} \cong 250 \text{ mA}$		0.4	0.6	nC
Input Capacitance	C <sub>iss</sub>			30		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz		6		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	I = I IVITZ		2.5		
Switching <sup>a, b, c</sup>				<u> </u>		
Turn-On Time	t <sub>d(on)</sub>	$V_{DD}$ = 30 V, $R_{L}$ = 150 $\Omega$			25	
Turn-Off Time	t <sub>d(off)</sub>	$I_D \cong 200 \text{ mA}, V_{GEN} = 10 \text{ V}, R_G = 10 \Omega$			35	ns

#### Notes:

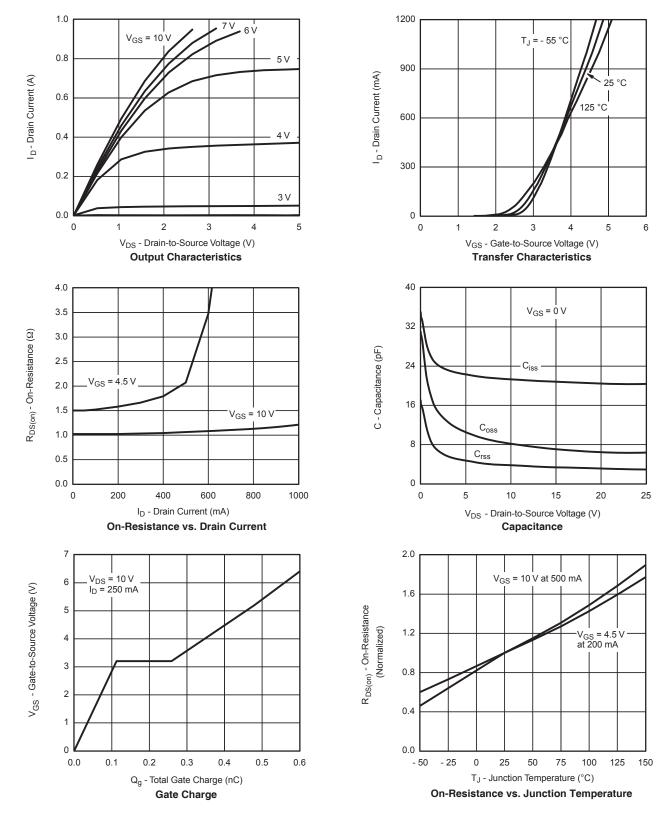
- a. For DESIGN AID ONLY, not subject to production testing. b. Pulse test: PW  $\leq$  300  $\mu$ s duty cycle  $\leq$  2 %. c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



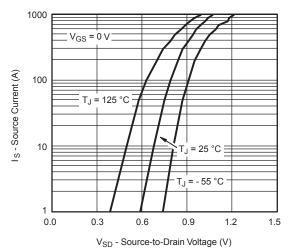
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

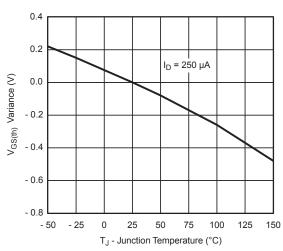




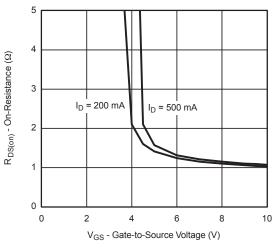
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



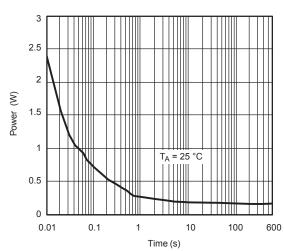
Source-Drain Diode Forward Voltage



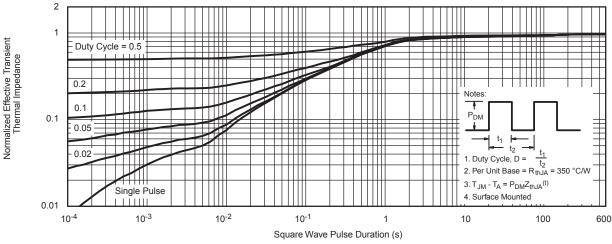
Threshold Voltage Variance Over Temperature



On-Resistance vs. Gate-Source Voltage



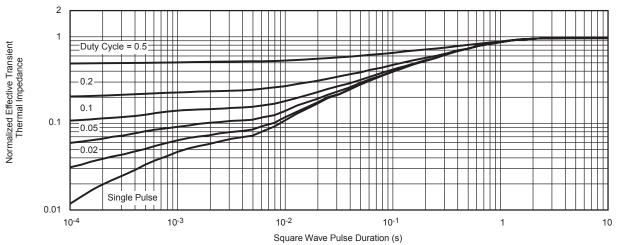
Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C )

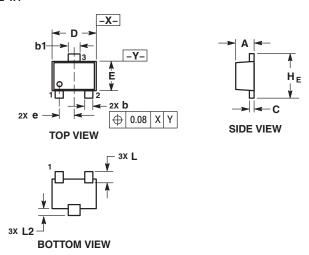
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



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#### SOT-723





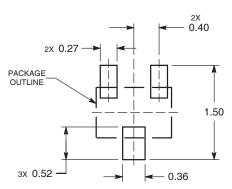
#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
Е	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
Г	0.29 REF		
L2	0.15	0.20	0.25

### RECOMMENDED **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS



## Din-Tek SEMICONDUCTOR

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